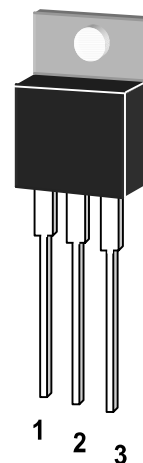


SD13007

NPN Silicon Transistor
for high-voltage,high-speed power switching .



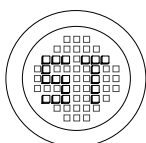
1. Base 2. Collector 3. Emitter

TO-220 Plastic Package

Absolute Maximum Ratings ($T_a=25\text{ }^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	700	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	9	V
Collector Current	I_C	8	A
Power Dissipation	P_{tot}	80	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_S	-55 to +150	$^{\circ}\text{C}$

G S P FORM A IS AVAILABLE



®

РАДИОТЕХ

Тел.: (495) 795-0805
Факс: (495) 234-1603
Эл. почта: info@rct.ru
Веб: www.rct.ru

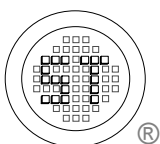
SD13007

Characteristics at Ta=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=5V$, $I_C=2A$	h_{FE}	10	-	70	-
Collector Emitter Breakdown Voltage at $I_C=10mA$	$V_{(BR)CEO}$	400	-	-	V
Collector Base Breakdown Voltage at $I_C=100\mu A$	$V_{(BR)CBO}$	700	-	-	V
Emitter Base Breakdown Voltage at $I_E=1mA$	$V_{(BR)EBO}$	9	-	-	V
Collector Cutoff Current at $V_{CB}=700V$	I_{CBO}	-	-	100	μA
Emitter Cutoff Current at $V_{EB}=9V$	I_{EBO}	-	-	100	μA
Collector-Emitter Saturation Voltage at $I_C=5A$, $I_B=1A$	$V_{CE(sat)}$	-	-	2	V
Base-Emitter Saturation Voltage at $I_C=5A$, $I_B=1A$	$V_{BE(sat)}$	-	-	1.6	V
Current-Gain-Bandwidth Product at $V_{CE}=10V$, $I_C=0.5A$	f_T	4	-	-	MHz
Output Capacitance at $V_{CB}=10V$, $f=0.1MHz$	C_{OB}	-	110	-	pF

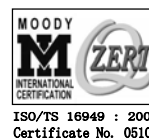
Pulse Test: Pulse Width \leq 300 μs , Duty Cycle \leq 2%.

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 550-100-02-002-001

Dated : 07/12/2002